

# Wenhao Chen

## List of Publications by Year in descending order

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21  
papers

538  
citations

758635

12  
h-index

887659

17  
g-index

22  
all docs

22  
docs citations

22  
times ranked

974  
citing authors

#	ARTICLE	IF	CITATIONS
1	SiO <sub>2</sub> -Based Conductive-Bridging Random Access Memory. Kluwer International Series in Electronic Materials: Science and Technology, 2022, , 147-186.	0.3	0
2	<i>In Situ</i> ; Synaptic Programming of CBRAM in an Ionizing Radiation Environment. IEEE Transactions on Nuclear Science, 2018, 65, 192-199.	1.2	5
3	SiO <sub>2</sub> based conductive bridging random access memory. Journal of Electroceramics, 2017, 39, 109-131.	0.8	32
4	Total-Ionizing-Dose Effects on Resistance Stability of Programmable Metallization Cell Based Memory and Selectors. IEEE Transactions on Nuclear Science, 2017, 64, 269-276.	1.2	11
5	Low-Temperature Characterization of Cu@Cu:Silica-Based Programmable Metallization Cell. IEEE Electron Device Letters, 2017, 38, 1244-1247.	2.2	15
6	A Comparative Study on TID Influenced Lateral Diffusion of Group 11 Metals into GeS <sub>1-x</sub> and Ge <sub>x</sub> Se <sub>1-x</sub> Systems: A Flexible Radiation Sensor Development Perspective. IEEE Transactions on Nuclear Science, 2017, , 1-1.	1.2	0
7	Ag-chalcogenide glass flexible radiation sensor: Impact of atomic ratio of Se on the TID influenced lateral diffusion of Ag. , 2016, , .		1
8	Flexible Ag-ChG Radiation Sensors: Limit of Detection and Dynamic Range Optimization Through Physical Design Tuning. IEEE Transactions on Nuclear Science, 2016, 63, 2137-2144.	1.2	7
9	Demonstration of spike timing dependent plasticity in CBRAM devices with silicon neurons. , 2016, , .		12
10	Impedance Spectroscopy of Programmable Metallization Cells With a Thin SiO <sub>2</sub> Switching Layer. IEEE Electron Device Letters, 2016, 37, 576-579.	2.2	9
11	Radiation Hardening by Process of CBRAM Resistance Switching Cells. IEEE Transactions on Nuclear Science, 2016, 63, 2145-2151.	1.2	15
12	A CMOS-compatible electronic synapse device based on Cu/SiO <sub>2</sub> /W programmable metallization cells. Nanotechnology, 2016, 27, 255202.	1.3	66
13	Volatile and Non-Volatile Switching in Cu-SiO <sub>2</sub> Programmable Metallization Cells. IEEE Electron Device Letters, 2016, 37, 580-583.	2.2	87
14	A Study of Gamma-Ray Exposure of Cu@SiO <sub>2</sub> Programmable Metallization Cells. IEEE Transactions on Nuclear Science, 2015, 62, 2404-2411.	1.2	24
15	TID Impact on Process Modified CBRAM Cells. , 2015, , .		6
16	Low-Temperature Characteristics of HfO <sub>2</sub> -Based Resistive Random Access Memory. IEEE Electron Device Letters, 2015, 36, 567-569.	2.2	85
17	<i>In Situ</i> TEM Imaging of Defect Dynamics under Electrical Bias in Resistive Switching Rutile-TiO <sub>2</sub> . Microscopy and Microanalysis, 2015, 21, 140-153.	0.2	42
18	Total ionizing dose effect of <sup>60</sup> Co-ray radiation on the switching characteristics and filament stability of HfO <sub>x</sub> resistive random access memory. Applied Physics Letters, 2014, 104, .	1.5	57

#	ARTICLE	IF	CITATIONS
19	Dislocation impact on resistive switching in single-crystal SrTiO <sub>3</sub> . Journal of Applied Physics, 2013, 113, .	1.1	24
20	Elimination of high transient currents and electrode damage during electroformation of TiO <sub>2</sub> -based resistive switching devices. Journal Physics D: Applied Physics, 2012, 45, 395101.	1.3	20
21	Fabrication and luminescent properties of red phosphor M <sub>3</sub> BO <sub>6</sub> :Eu <sup>3+</sup> (M=La, Y). Journal of Rare Earths, 2010, 28, 295-298.	2.5	18